Ordering number : ENN6618

N-Channel Silicon MOSFET

FW232

Load Switching Applications

Features

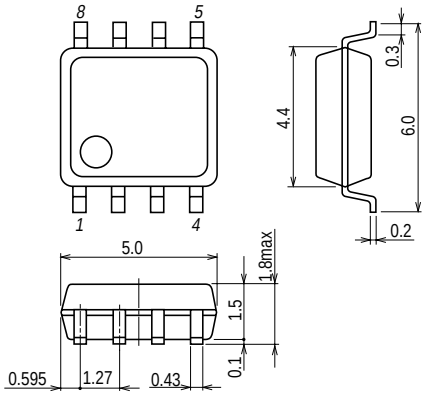
- Low ON-resistance.
- 2.5V drive.

Package Dimensions

unit : mm

2129

[FW232]



1 : Source1
2 : Gate1
3 : Source2
4 : Gate2
5 : Drain2
6 : Drain2
7 : Drain1
8 : Drain1

SANYO : SOP8

Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V_{DSS}		30	V
Gate-to-Source Voltage	V_{GSS}		±10	V
Drain Current (DC)	I_D		8	A
Drain Current (Pulse)	I_{DP}	PW≤10μs, duty cycle≤1%	52	A
Allowable Power Dissipation	P_D	Mounted on a ceramic board (1000mm²×0.8mm) 1unit	1.7	W
Total Dissipation	P_T	Mounted on a ceramic board (1000mm²×0.8mm)	2.0	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		-55 to +150	°C

Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	I_D=1mA, V_{GS}=0	30			V
Zero-Gate Voltage Drain Current	I_{DSS}	V_{DS}=30V, V_{GS}=0			1	μA
Gate-to-Source Leakage Current	I_{GSS}	V_{GS}=±8V, V_{DS}=0			±10	μA
Cutoff Voltage	$V_{GS(off)}$	V_{DS}=10V, I_D=1mA	0.4		1.3	V
Forward Transfer Admittance	$\|yfs\|$	V_{DS}=10V, I_D=8A	16	22		S

Marking : W232

Continued on next page.

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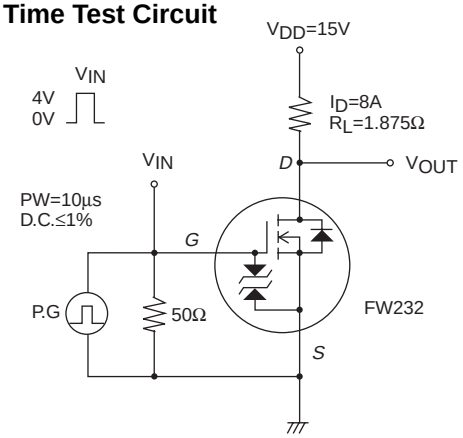
TOKYO OFFICE Tokyo Bldg., 1-10, 1 Chome, Ueno, Taito-ku, TOKYO, 110-8534 JAPAN

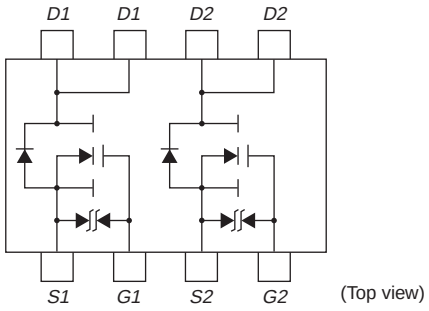
Continued from preceding page.

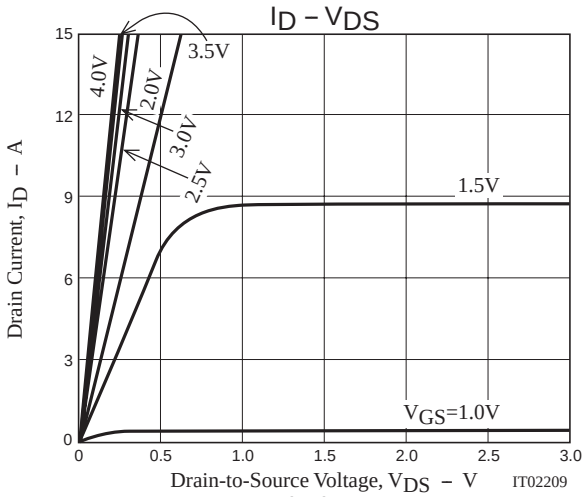
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Static Drain-to-Source On-State Resistance	$R_{DS}(on)1$	I_D=8A, V_{GS}=4V		17	23	mΩ
	$R_{DS}(on)2$	I_D=2A, V_{GS}=2.5V		23	32	mΩ
Input Capacitance	Ciss	V_{DS}=10V, f=1MHz		1550		pF
Output Capacitance	Coss	V_{DS}=10V, f=1MHz		310		pF
Reverse Transfer Capacitance	Crss	V_{DS}=10V, f=1MHz		190		pF
Turn-ON Delay Time	$t_d(on)$	See specified Test Circuit		22		ns
Rise Time	t_r	See specified Test Circuit		110		ns
Turn-OFF Delay Time	$t_d(off)$	See specified Test Circuit		200		ns
Fall Time	t_f	See specified Test Circuit		170		ns
Total Gate Charge	Qg	V_{DS}=10V, V_{GS}=10V, I_D=8A		60		nC
Gate-to-Source Charge	Qgs	V_{DS}=10V, V_{GS}=10V, I_D=8A		2.6		nC
Gate-to-Drain “Miller” Charge	Qgd	V_{DS}=10V, V_{GS}=10V, I_D=8A		10		nC
Diode Forward Voltage	V_{SD}	I_S=8A, V_{GS}=0		0.9	1.2	V

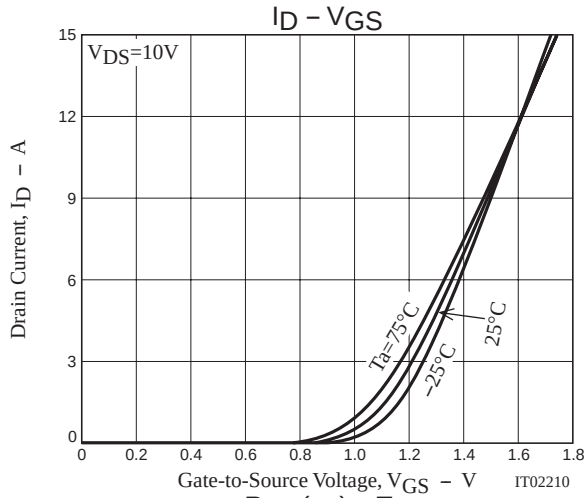
Switching Time Test Circuit

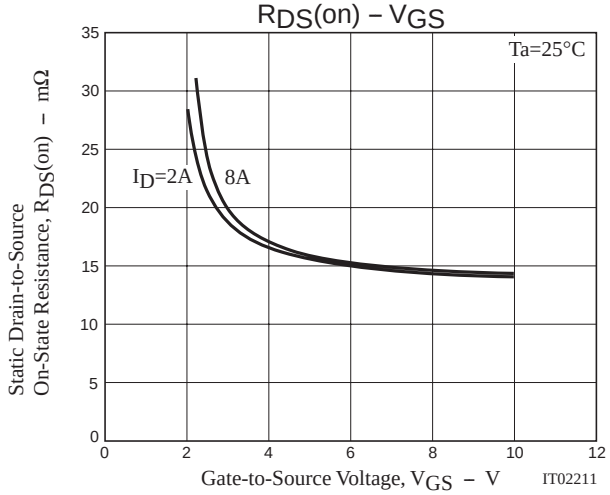


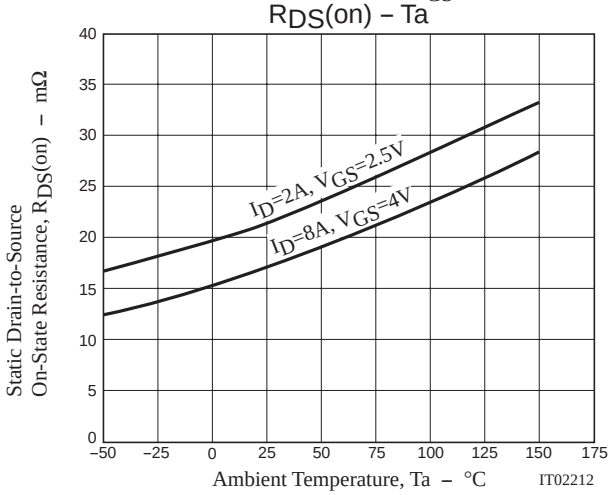
Electrical Connection

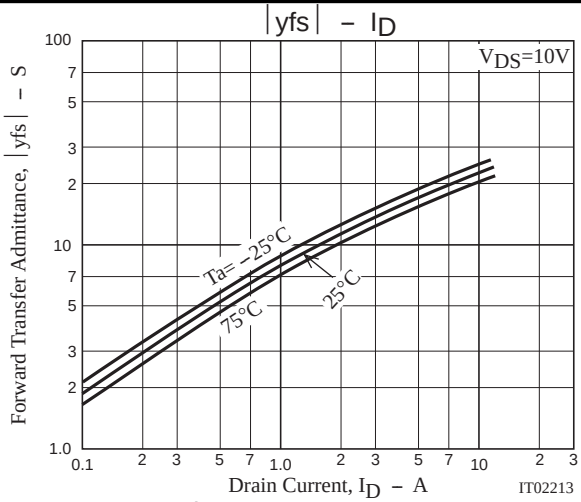


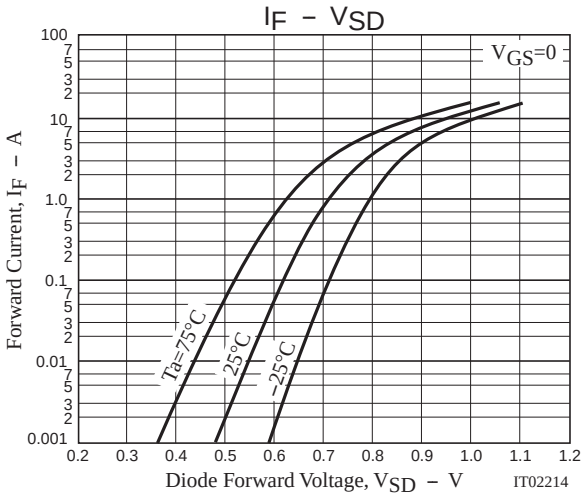


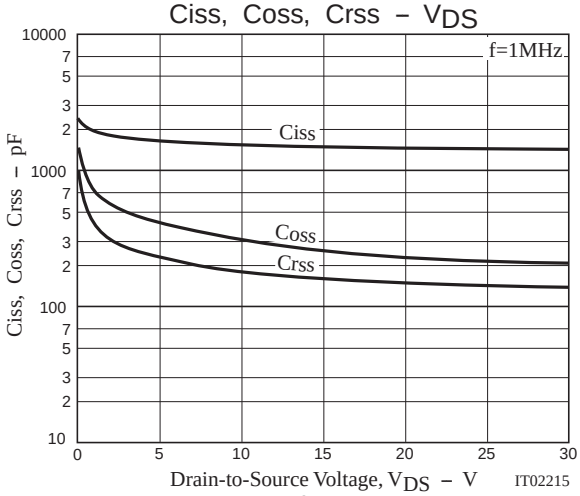


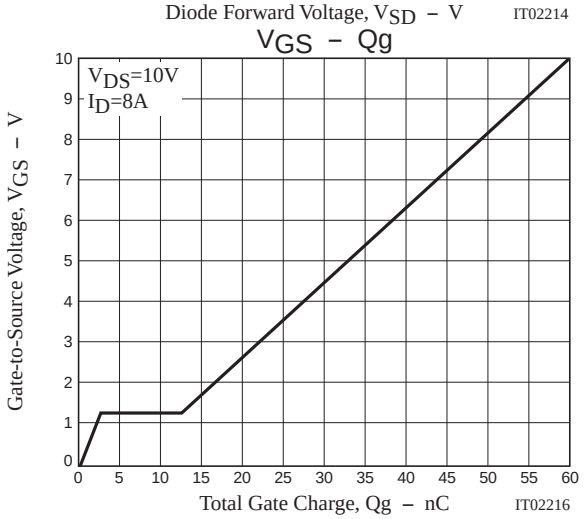


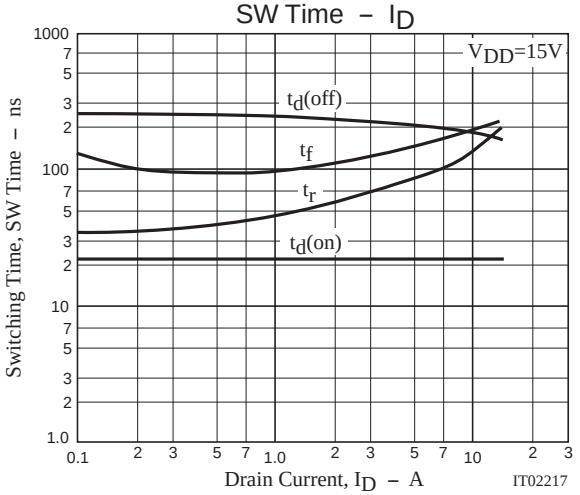


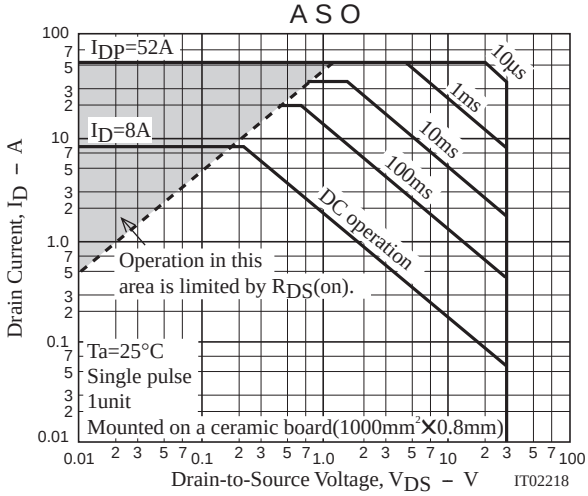

|yfs| – ID
VDS=10V
Ta= –25°C
75°C
25°C
Forward Transfer Admittance, |yfs| – S
Drain Current, ID – A
IT02213

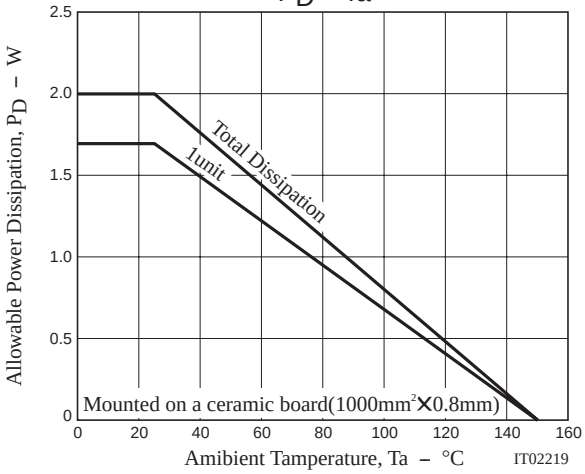

IF – VSD
VGS=0
Ta=75°C
25°C
–25°C
Forward Current, IF – A
Diode Forward Voltage, VSD – V
IT02214


Ciss, Coss, Crss – VDS
f=1MHz
Ciss
Coss
Crss
Ciss, Coss, Crss – pF
Drain-to-Source Voltage, VDS – V
IT02215


VGS – Qg
VDS=10V
ID=8A
Gate-to-Source Voltage, VGS – V
Total Gate Charge, Qg – nC
IT02216


SW Time – ID
VDD=15V
td(off)
tf
tr
td(on)
Switching Time, SW Time – ns
Drain Current, ID – A
IT02217


A S O
IDP=52A
ID=8A
10μs
1ms
10ms
100ms
DC operation
Operation in this
area is limited by RDS(on).
Ta=25°C
Single pulse
1unit
Mounted on a ceramic board(1000mm²×0.8mm)
Drain Current, ID – A
Drain-to-Source Voltage, VDS – V
IT02218


PD – Ta
Total Dissipation
1unit
Mounted on a ceramic board(1000mm²×0.8mm)
Allowable Power Dissipation, PD – W
Amibient Tamperature, Ta – °C
IT02219

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